

KSA1182

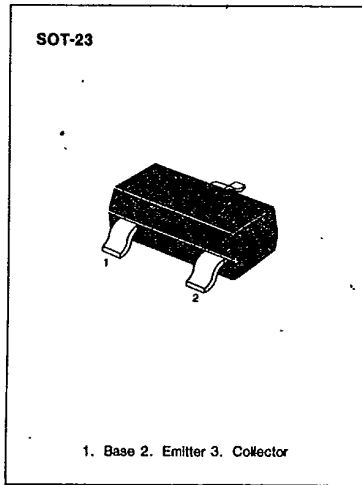
PNP EPTAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

• Complement to KSA2859

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-35	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-500	mA
Collector Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C



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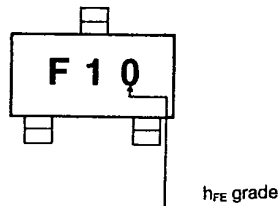
ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = -35V, I _E = 0			-0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC Current Gain	h _{FE1}	V _{CE} = -1V, I _C = -100mA	70		240	
	h _{FE2}	V _{CE} = -6V, I _C = -400mA	25			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA		-0.1	-0.25	V
Base-Emitter On Voltage	V _{BE(on)}	I _C = -100mA, V _{CE} = -1V		-0.8	-1.0	V
Current Gain-Bandwidth Product	f _T	I _C = -20mA, V _{CE} = -6V		200		MHz
Output Capacitance	C _{ob}	V _{CB} = -6V, I _E = 0 f = 1MHz		13		pF

h_{FE} CLASSIFICATION

Classification	O	Y
h _{FE} (1)	70-140	120-240

Marking

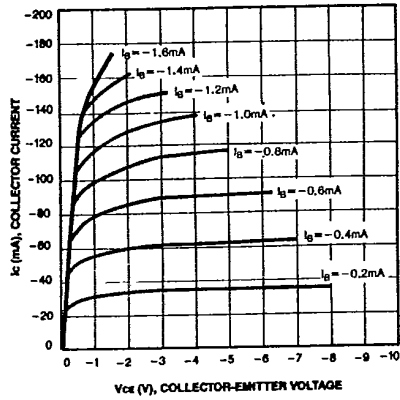


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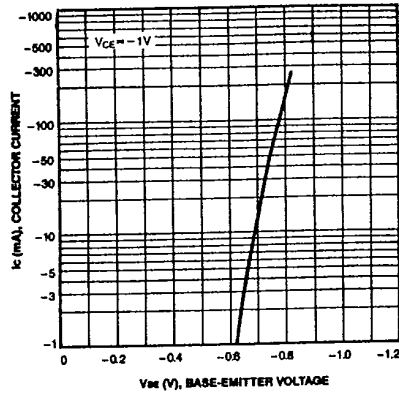
PNP EPITAXIAL SILICON TRANSISTOR

T-29-15

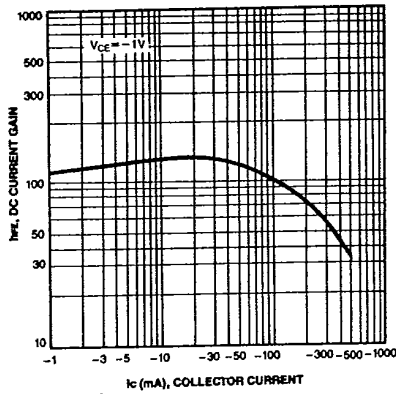
STATIC CHARACTERISTIC



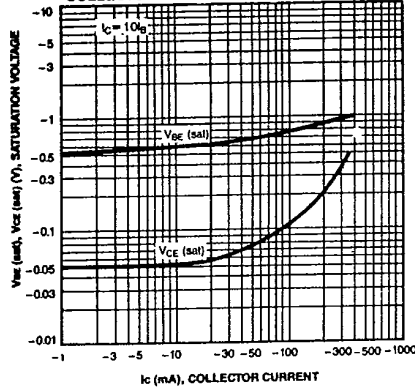
BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN



**BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE**



COLLECTOR OUTPUT CAPACITANCE

